

Vishay Siliconix

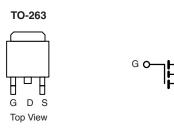
RoHS

COMPLIANT HALOGEN

FREE

Automotive P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	- 40			
$R_{DS(on)}(\Omega)$ at V_{GS} = - 10 V	0.0040			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 V$	0.0060			
I _D (A)	- 120			
Configuration	Single			



P-Channel MOSFET

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FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified^d
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

ORDERING INFORMATION			
Package	TO-263		
Lead (Pb)-free and Halogen-free	SQM110P04-04L-GE3		

ABSOLUTE MAXIMUM RATINGS ($T_c = 25 \degree C$, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	- 40	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current ^a	T _C = 25 °C	- I _D -	- 120		
	T _C = 125 °C		- 120		
Continuous Source Current (Diode Conduction) ^a		I _S	- 120	А	
Pulsed Drain Current ^b		I _{DM}	- 330		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 80		
Single Pulse Avalanche Energy		E _{AS}	320	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	р	375	W	
	T _C = 125 °C	P _D	125		
Operating Junction and Storage Temperature Range		TJ, T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.40	0/10	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).

d. Parametric verification ongoing.

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SPECIFICATIONS ($T_C = 25 \text{ °C}$, unless otherwise noted)								
PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static		•					•	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0, I_D = -250 \ \mu A$		- 40	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = - 250 μA	- 1.5	- 2.0	- 2.5	v	
Gate-Source Leakage	I _{GSS}	$V_{DS} =$	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = - 40 V	-	-	- 1.0		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V_{DS} = - 40 V, T_J = 125 °C	-	-	- 50	μA	
		$V_{GS} = 0 V$	V_{DS} = - 40 V, T_J = 175 °C	-	-	- 250		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = -10 V$	$V_{DS} \le$ - 5 V	- 120	-	-	Α	
Drain-Source On-State Resistance ^a		$V_{GS} = -10 V$	I _D = - 30 A	-	0.0034	0.0040	Ω	
	В	$V_{GS} = -10 V$	$I_D = -30 \text{ A}, \text{ T}_J = 125 \text{ °C}$	-	-	0.0059		
	R _{DS(on)}	$V_{GS} = -10 V$	I _D = - 30 A, T _J = 175 °C	-	-	0.0070		
		$V_{GS} = -4.5 V$	I _D = - 20 A	-	0.0050	0.0060		
Forward Transconductanceb	9 _{fs}	V _{DS} = - 15 V, I _D = - 30 A		-	97	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}		V _{DS} = - 20 V, f = 1 MHz	-	11 183	13 980	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	1614	2020		
Reverse Transfer Capacitance	C _{rss}			-	1294	1620		
Total Gate Charge ^c	Qg		V _{DS} = - 20 V, I _D = - 110 A	-	220	330	nC	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V		-	34	-		
Gate-Drain Charge ^c	Q _{gd}			-	56	-		
Gate Resistance	Rg		f = 1 MHz	1.2	2.5	3.7	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	17	26		
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{DD}=\text{-}~20~\text{V},~\text{R}_{L}=0.18~\Omega\\ \text{I}_{D}\cong\text{-}~110~\text{A},~\text{V}_{GEN}=\text{-}~10~\text{V},~\text{R}_{g}=1~\Omega \end{array}$		-	15	23	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	112	168		
Fall Time ^c	t _f			-	45	68		
Source-Drain Diode Ratings and Char	acteristics ^b				·		·	
Pulsed Current ^a	I _{SM}			-	-	- 330	Α	
Forward Voltage	V _{SD}	I _F = - 100 A, V _{GS} = 0		-	- 0.95	- 1.5	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

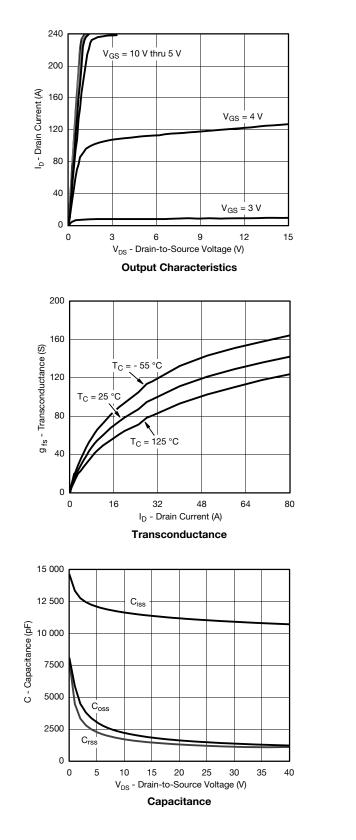
c. Independent of operating temperature.

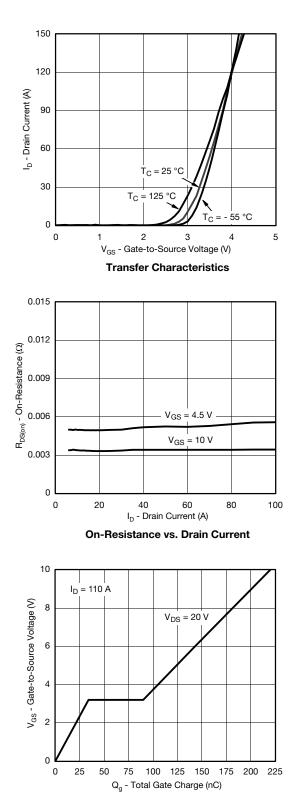
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)





Gate Charge

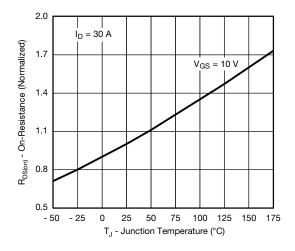
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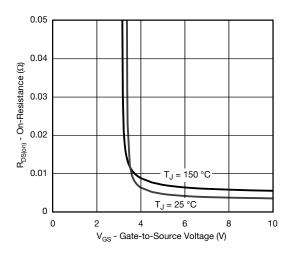


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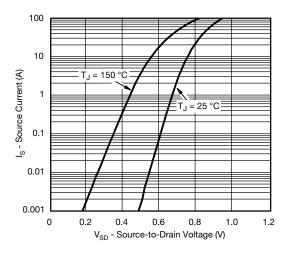
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



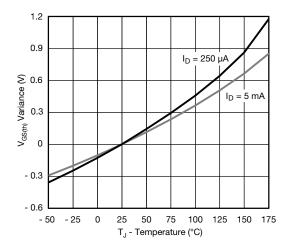
On-Resistance vs. Junction Temperature



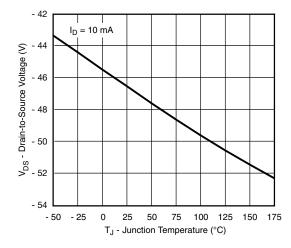
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

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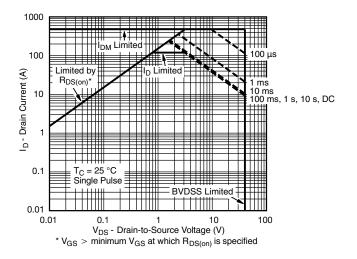
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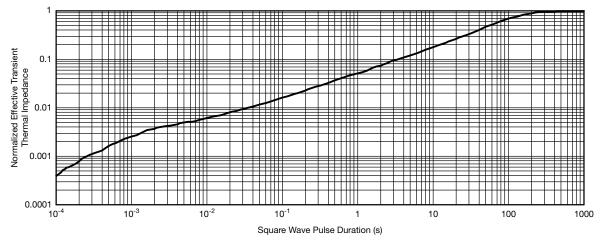


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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area

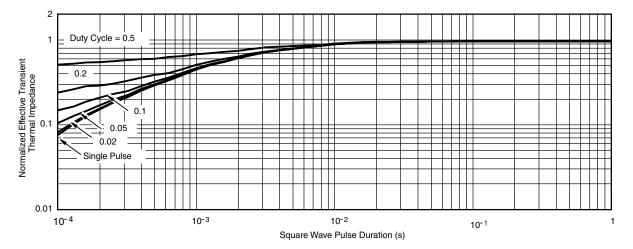


Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg265268.



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